

DE2S06200L

Silicon epitaxial planar type

For ESD protection

■ Features

- High ESD
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: E1

■ Packaging

Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

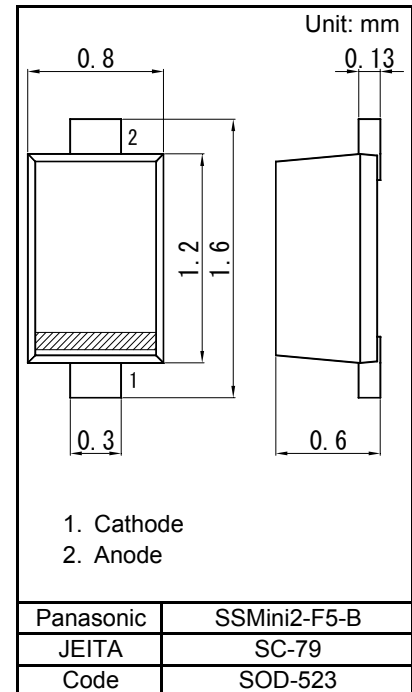
■ Absolute Maximum Ratings Ta = 25 °C

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|--------|-------------|------|
| Total power dissipation ^{*1} | PT | 150 | mW |
| Electrostatic discharge ^{*2} | ESD | ±30 | kV |
| Junction temperature | Tj | 150 | °C |
| Operating ambient temperature | Topr | -40 to +85 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

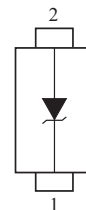
Note) *1: Mounted on glass epoxy print board. (45 mm x 45 mm x 1 mm)

Solder in (0.8 mm x 0.6 mm)

*2: Test method: IEC61000_4_2(C = 150 pF, R = 330 Ω, Contact discharge: 10 times)



Internal Connection



■ Electrical Characteristics Ta = 25 °C ± 3 °C

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|--------|---------------------|------|-----|------|-------|
| Zener voltage ^{*1,*2} | VZ | IZ = 1 mA | 5.89 | | 6.51 | V |
| Reverse current | IR | VR = 4 V | | | 1.0 | μA |
| Terminal capacitance | Ct | VR = 0 V, f = 1 MHz | | 55 | | pF |
| Temperature coefficient of zener voltage ^{*3} | SZ | IZ = 1 mA | | 2.3 | | mV/°C |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. *1: The temperature must be controlled 25°C for VZ measurement.

VZ value measured at other temperature must be adjusted to VZ (25°C)

*2: VZ guaranteed 20 ms after current flow.

*3: Tj = 25°C to 150°C